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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
. 10/552,513	10/06/2005	Yasushi Araki	Q90689	2406
23373 7590 04/16/2007 SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. SUITE 800 WASHINGTON, DC 20037			EXAMINER	
			COLEMAN, WILLIAM D	
			ART UNIT	PAPER NUMBER
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SHORTENED STATUTORY PERIOD OF RESPONSE MAIL DATE		DELIVERY MODE		
3 MON		04/16/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

1) Notice of References Cited (PTO-892)

Paper No(s)/Mail Date 10/05.

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO/SB/08)

4) Interview Summary (PTO-413)

Paper No(s)/Mail Date __

6) Other:

Notice of Informal Patent Application

Application/Control Number: 10/552,513

Art Unit: 2823

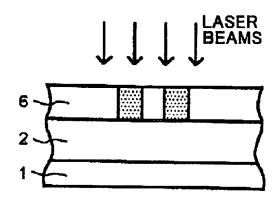
DETAILED ACTION

Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Rejections - 35 USC § 102

- (a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.
- 2. Claims 1-5 and 7-9 are rejected under 35 U.S.C. 102(a) as being anticipated by Okumura et al., U.S. Patent Application Publication No. U.S. 2002/0139972 A1.



3. Pertaining to claim 1, Okumura teaches a method for producing a substrate having a Si layer comprising the steps of forming an amorphous Si layer 6 on a plastic substrate 1, and irradiating said amorphous Si layer with a laser beam to crystallize said amorphous Si, wherein said plastic substrate has light transmittance of 30 to 100% at an oscillation wavelength of said laser beam (please note that the Examiner takes the position that since Okumura teaches a plastic substrate comprising (PES) polyethersulfone {see paragraph [0100] of Okumura} the light transmittance is inherently 30 to 100% at a laser oscillation wavelength as disclosed on page 3 of Applicants disclosure).

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4. Pertaining to claim 2, Okumura teaches the method of claim 1 for producing a substrate

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having a crystalline Si layer, wherein said amorphous Si layer has a thickness of 1 to 2,000 nm

(see paragraph [0101] where Okumura teaches an amorphous silicon film having a thickness of

500 angstroms which is equivalent to 50 nanometers i.e., 50 nm).

5. Pertaining to claim 3, Okumura teaches the method of claim 1 for producing a substrate

having a crystalline Si layer, wherein the oscillation wavelength of said layer beam is 140 to 450

nm (please note that Okumura teaches a xenon chloride XeCl light source which is well known

to emit light in the ultraviolet wavelength see paragraph [0113]).

6. Pertaining to claim 4, Okumura teaches the method of claim 1 for producing a substrate

having a crystalline Si layer, wherein said laser is an excimer laser (please see the rejection of

claim 3 above).

7. Pertaining to claim 5, Okumura teaches the method of claim 1 for producing a substrate

having a crystalline Si layer, wherein said plastic substrate is made of amorphous polyolefin or

polysethersulfone (please see the rejection of claim 1 above).

8. Pertaining to claim 7, Okumura teaches a substrate having a crystalline Si layer produced

by the method recited in claim 1.

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9. Pertaining to claim 8, Okumura teaches the substrate of claim 7 having a crystalline Si layer, wherein said plastic substrate is provided with an insulating thin film 2 having a thickness of 10 nm to 10 um on at least one surface.

- 10. Pertaining to claim 9, <u>Okumura</u> teaches a crystalline Si device comprising the substrate of claim 7 having a crystalline Si layer.
- 11. Claim 6 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

- 12. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 571-272-1856. The examiner can normally be reached on Monday-Friday 9:00 AM 5:30 PM.
- 13. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matt Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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14. Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

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like assistance from a USPTO Customer Service Representative or access to the automated

information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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WDC